

UNIT

V

Ω

nC

# **N-Channel Power MOSFET**

600V, 4.0A, 2.5Ω

### **FEATURES**

- 100% Avalanche Tested
- Pb-free plating •
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition •

# **APPLICATION**

- Power Supply
- Lighting







**KEY PERFORMANCE PARAMETERS** 

VALUE

600

2.5

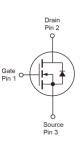
14.5

PARAMETER

 $V_{DS}$ 

R<sub>DS(on)</sub> (max)

Qg



HALOGEN

Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (D-PAK) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER		SYMBOL	IPAK/DPAK ITO-220		UNIT	
Drain-Source Voltage		V <sub>DS</sub>	600		V	
Gate-Source Voltage		$V_{GS}$	±30		V	
Continuous Drain Current (Note 1)	<sub>c</sub> = 25°C		4.0		A	
T <sub>c</sub>	c= 100°C	I <sub>D</sub>	2.4			
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	16	i	А	
Total Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>DTOT</sub>	50	25	W	
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	70		mJ	
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	4		А	
Repetitive Avalanche Energy (Note 2)		E <sub>AR</sub>	5		mJ	
Peak Diode Recovery (Note 4)		dV/dt	4.5	5	V/ns	
Operating Junction and Storage Temperatur	e Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to	+150	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	IPAK/DPAK	ITO-220	UNIT	
Junction to Case Thermal Resistance	R <sub>ejc</sub>	2.5	5	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	83	62.5	°C/W	

Notes: ReJA is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design. R<sub>0JA</sub> shown below for single device operation on FR-4 PCB in still air.



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ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 5)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV <sub>DSS</sub>	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V <sub>GS(TH)</sub>	2.5	3.5	4.5	V
Gate Body Leakage	$V_{GS} = \pm 30 \text{V},  V_{DS} = 0 \text{V}$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.0A$	R <sub>DS(on)</sub>		2.2	2.5	Ω
Forward Transfer Conductance	$V_{DS} = 40V, I_{D} = 2A$	<b>g</b> <sub>fs</sub>		2.6		S
Dynamic <sup>(Note 6)</sup>						
Total Gate Charge		Qg		14.5		
Gate-Source Charge	$V_{DS} = 480V, I_D = 4.0A,$	Q <sub>gs</sub>		3.4		nC
Gate-Drain Charge	V <sub>GS</sub> = 10V	Q <sub>gd</sub>		7		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>iss</sub>		500		
Output Capacitance		C <sub>oss</sub>		53.2		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		7		
Switching (Note 7)						
Turn-On Delay Time		t <sub>d(on)</sub>		11		
Turn-On Rise Time	$V_{DD} = 300V,$	t <sub>r</sub>		20		
Turn-Off Delay Time	$R_{GEN} = 25\Omega,$ $I_D = 4.0A, V_{GS} = 10V,$	t <sub>d(off)</sub>		30		ns
Turn-Off Fall Time		t <sub>f</sub>		19		
Source-Drain Diode (Note 5)	·					
Forward On Voltage	$I_{\rm S} = 4.0$ A, $V_{\rm GS} = 0$ V	V <sub>SD</sub>			1.13	V
Reverse Recovery Time	$V_{GS}=0V, I_{S}=2A$	t <sub>rr</sub>		522		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q <sub>rr</sub>		1.6		μC
Source Current	Integral reverse diode	I <sub>S</sub>			4	Α
Source Current (Pulse)	in the MOSFET	I <sub>SM</sub>			16	А

#### Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. L = 8mH, I\_{AS} = 4.0A, V\_{DD} = 50V, R\_G = 25\Omega, Starting T\_J = 25°C.

100% Eas Test Condition: L = 8mH,  $I_{AS}$  = 2A,  $V_{DD}$  = 50V,  $R_G$  = 25 $\Omega$ , Starting  $T_J$  = 25°C

- 4.  $I_{SD} \le 4A$ , dI/dt  $\le 200A/\mu s$ ,  $V_{DD} \le BV_{DSS}$ , Starting  $T_J = 25^{\circ}C$ .
- 5. Pulse test:  $PW \le 300\mu s$ , duty cycle  $\le 2\%$ .
- 6. For DESIGN AID ONLY, not subject to production testing.
- 7. Switching time is essentially independent of operating temperature.



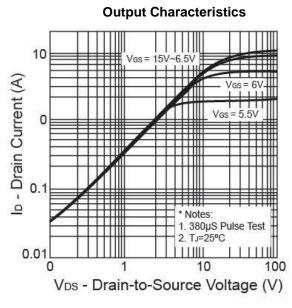
# **ORDERING INFORMATION**

ORDERING CODE	PACKAGE	PACKING
TSM4NB60CI C0G	ITO-220	50pcs / Tube
TSM4NB60CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM4NB60CH X0G	TO-251S (IPAK SL)	75pcs / Tube
TSM4NB60CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

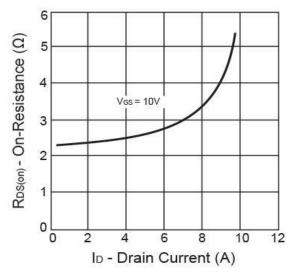


# **CHARACTERISTICS CURVES**

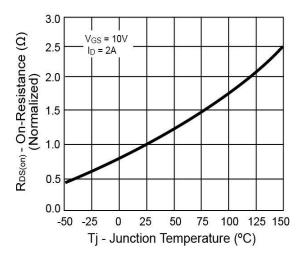
(T<sub>C</sub> = 25°C unless otherwise noted)

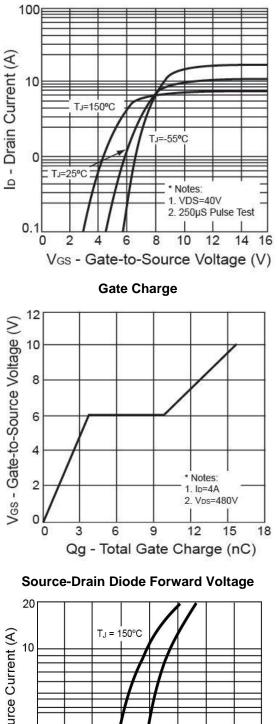


#### **On-Resistance vs. Drain Current**

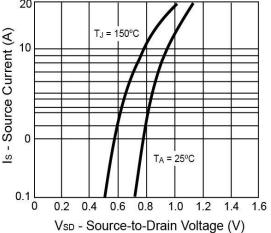


**On-Resistance vs. Junction Temperature** 





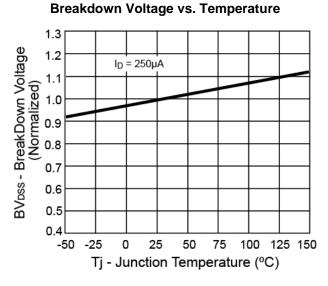
#### **Transfer Characteristics**



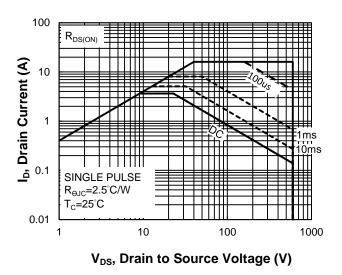


### **CHARACTERISTICS CURVES**

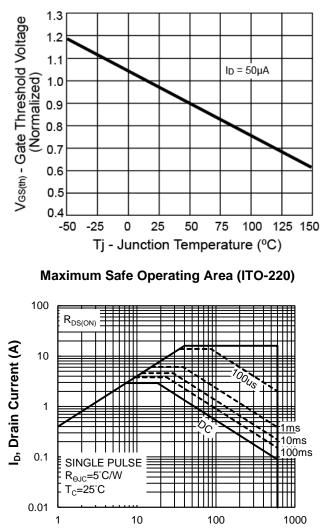
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 



Maximum Safe Operating Area (IPAK/DPAK)



Threshold Voltage vs. Temperature



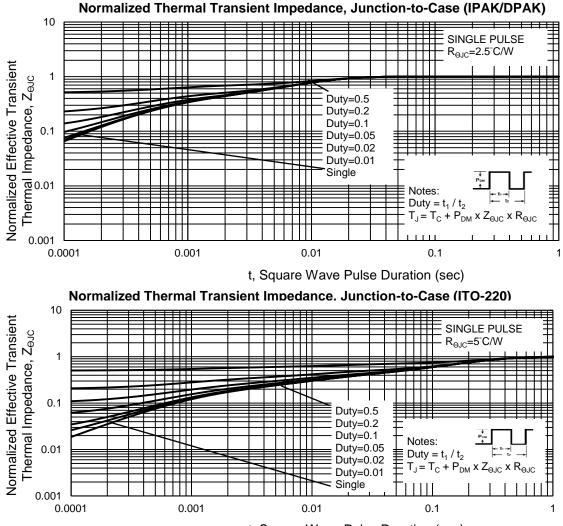
V<sub>DS</sub>, Drain to Source Voltage (V)





# **ELECTRICAL CHARACTERISTICS CURVES**

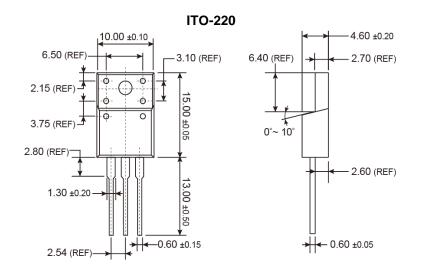
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$ 



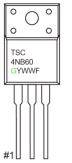
t, Square Wave Pulse Duration (sec)



# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



### **MARKING DIAGRAM**



- **G** = Halogen Free
- Y = Year Code
- WW = Week Code (01~52)
  - **F** = Factory Code

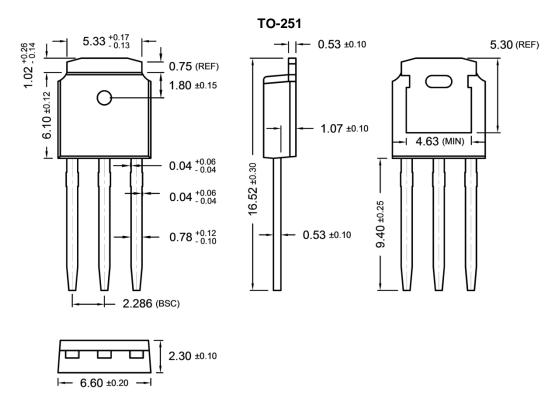
Version: L1901





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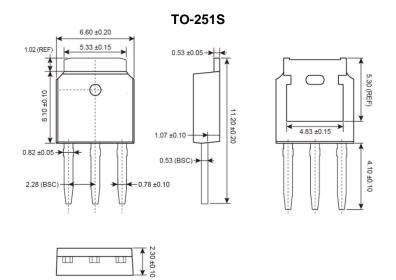
# **MARKING DIAGRAM**

<b>5</b> 0 4NB60	<ul><li>Y = Year Code</li><li>M = Month Code for Halogen Free Product</li></ul>
YML CH	<b>O</b> =Jan <b>P</b> =Feb <b>Q</b> =Mar <b>R</b> =Apr
	<b>S</b> =May <b>T</b> =Jun <b>U</b> =Jul <b>V</b> =Aug
	W =Sep X =Oct Y =Nov Z =Dec
	L = Lot Code (1~9, A~Z)





# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



### **MARKING DIAGRAM**



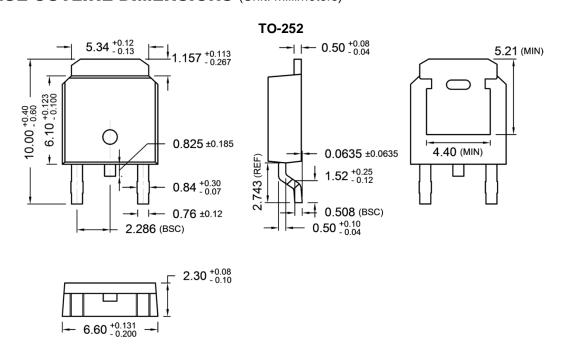
- Y = Year Code
- M = Month Code for Halogen Free Product
- **L** = Lot Code (1~9, A~Z)



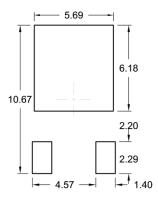


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**9**h



### SUGGESTED PAD LAYOUT (Unit: Millimeters)



# **MARKING DIAGRAM**

5	<ul><li>Y = Year Code</li><li>M = Month Code for Halogen Free Product</li></ul>	
4NB60 YMLOCP	<b>O</b> =Jan <b>P</b> =Feb <b>Q</b> =Mar <b>R</b>	=Apr
	S =May T =Jun U =Jul V	=Aug
	W =Sep X =Oct Y =Nov Z	=Dec
<i>••</i> 1	L = Lot Code (1~9, A~Z)	



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